SGS-THOMSON MICROELECTRONICS

IRF 620/FI-621/FI
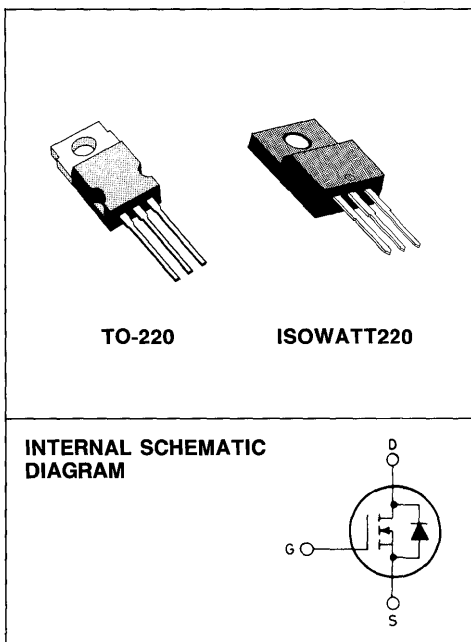# IRF 622/FI-623/FI

N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTORS

TYPE	V_{DSS}	$R_{DS(on)}$	I_D ■
IRF620	200 V	0.8 Ω	5 A
IRF620FI	200 V	0.8 Ω	4 A
IRF621	150 V	0.8 Ω	5 A
IRF621FI	150 V	0.8 Ω	4 A
IRF622	200 V	1.2 Ω	4 A
IRF622FI	200 V	1.2 Ω	3.5 A
IRF623	150 V	1.2 Ω	4 A
IRF623FI	150 V	1.2 Ω	3.5 A

- 200V FOR TELECOMMUNICATION APPLICATIONS
- ULTRA FAST SWITCHING
- RATED FOR UNCLAMPED INDUCTIVE SWITCHING (ENERGY TEST) ◆
- EASY DRIVE - REDUCES COST AND SIZE

INDUSTRIAL APPLICATIONS:
- SWITCHING MODE POWER SUPPLIES
- DC SWITCH
- ROBOTCS

N - channel enhancement mode POWER MOS field effect transistors. Easy drive and very fast switching times make these POWER MOS transistors ideal for high speed switching applications. Typical uses are in telecommunications, robotics, switching power supplies and as a DC switch.

TO-220 **ISOWATT220**

INTERNAL SCHEMATIC DIAGRAM

ABSOLUTE MAXIMUM RATINGS

		TO-220 ISOWATT220	620 620FI	621 621FI	622 622FI	623 623FI	
V_{DS} *	Drain-source voltage ($V_{GS}=0$)		200	150	200	150	V
V_{DGR} *	Drain-gate voltage ($R_{GS}=20$ KΩ)		200	150	200	150	V
V_{GS}	Gate-source voltage			±20			V
I_{DM} (•)	Drain current (pulsed)		20	20	16	16	A
			620	**621**	**622**	**623**	
I_D	Drain current (cont.) at $T_c=$ 25°C		5	5	4	4	A
I_D	Drain current (cont.) at $T_c=$ 100°C		3	3	2.5	2.5	A
			620FI	**621FI**	**622FI**	**623FI**	
I_D ■	Drain current (cont.) at $T_c=$ 25°C		4	4	3.5	3.5	A
I_D ■	Drain current (cont.) at $T_c=$ 100°C		2.5	2.5	2	2	A
			TO-220		**ISOWATT220**		
P_{tot}	Total dissipation at $T_c<25°C$		40		30		W
	Derating factor		0.32		0.24		W/°C
T_{stg}	Storage temperature			− 55 to 150			°C
T_j	Max. operating junction temperature			150			°C

* $T_j = 25°C$ to $125°C$
(•) Repetitive Rating: Pulse width limited by max junction temperature.
■ See note on ISOWATT220 on this datasheet.
◆ Introduced in 1988 week 44

THERMAL DATA

			TO-220	ISOWATT220	
$R_{thj-case}$	Thermal resistance junction-case	max	3.12	4.16	°C/W
R_{thc-s}	Thermal resistance case-sink	typ	0.5		°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient	max	80		°C/W
T_l	Maximum lead temperature for soldering purpose		300		°C

ELECTRICAL CHARACTERISTICS ($T_{case} = 25°C$ unless otherwise specified)

Parameters		Test Conditions	Min.	Typ.	Max.	Unit

OFF

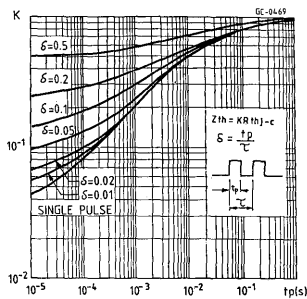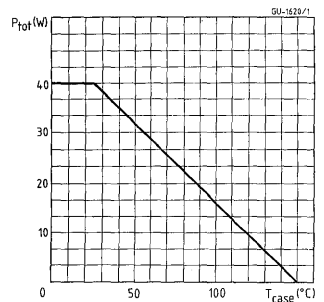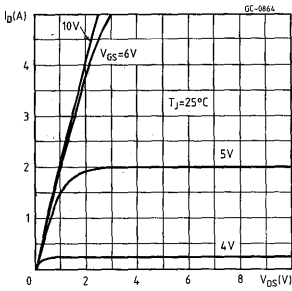|			Min.	Typ.	Max.	Unit
$V_{(BR) DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu A$ $V_{GS} = 0$ for **IRF620/622/620FI/622FI** for **IRF621/623/621FI/623FI**	200 150			V V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	V_{DS} = Max Rating V_{DS} = Max Rating x 0.8 $T_c = 125°C$			250 1000	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\ V$			± 500	nA

ON **

			Min.	Typ.	Max.	Unit
$V_{GS (th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ $I_D = 250\ \mu A$	2		4	V
$I_{D(on)}$	On-state drain current	$V_{DS} > I_{D (on)} \times R_{DS(on)\ max}$ $V_{GS} = 10\ V$ for **IRF620/621/620FI/621FI** for **IRF622/623/622FI/623FI**	5 4			A A
$R_{DS (on)}$	Static drain-source on resistance	$V_{GS} = 10\ V$ $I_D = 2.5\ A$ for **IRF620/621/620FI/621FI** for **IRF622/623/622FI/623FI**			0.8 1.2	Ω Ω

ENERGY TEST

			Min.	Typ.	Max.	Unit
I_{UIS}	Unclamped inductive switching current (single pulse)	$V_{DD} = 30\ V$ $L = 100\ \mu H$ starting $T_j = 25°C$ for **IRF620/621/620FI/621FI** for **IRF622/623/622FI/623FI**	5 4			A A

DYNAMIC

			Min.	Typ.	Max.	Unit
g_{fs} **	Forward transconductance	$V_{DS} > I_{D (on)} \times R_{DS (on)\ max}$ $I_D = 2.5\ A$	1.3			mho
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\ V$ $f = 1\ MHz$ $V_{GS} = 0$			600 300 80	pF pF pF

SGS-THOMSON MICROELECTRONICS

ELECTRICAL CHARACTERISTICS (Continued)

Parameters		Test Conditions	Min.	Typ.	Max.	Unit
SWITCHING						
$t_{d\,(on)}$	Turn-on time	$V_{DD} = 75$ V $I_D = 2.5$ A			40	ns
t_r	Rise time	$R_i = 50$ Ω			60	ns
$t_{d\,(off)}$	Turn-off delay time	(see test circuit)			100	ns
t_f	Fall time				60	ns
Q_g	Total Gate Charge	$V_{GS} = 10$ V $I_D = 6$ A $V_{DS} = $ Max Rating x 0.8 (see test circuit)			15	nC
SOURCE DRAIN DIODE						
I_{SD}	Source-drain current				5	A
I_{SDM} (•)	Source-drain current (pulsed)				20	A
V_{SD}**	Forward on voltage	for **IRF620/621/620FI/621FI** $I_{SD} = 5$ A $V_{GS} = 0$			1.8	V
		for **IRF622/623/622FI/623FI** $I_{SD} = 4$ A $V_{GS} = 0$			1.4	V
t_{rr}	Reverse recovery time			350		ns
Q_{rr}	Reverse recovered charge	$I_{SD} = 5$ A $di/dt = 100$ A/μs		2.3		μC

** Pulsed: Pulse duration $\leqslant$ 300 μs, duty cycle $\leqslant$ 1.5%
(•) Repetitive Rating: Pulse width limited by max junction temperature
■ See note on ISOWATT220 In this datasheet

Safe operating areas (standard package)

Thermal impedance (standard package)

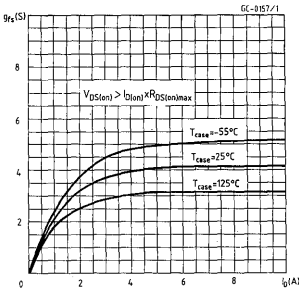Derating curve (standard package)

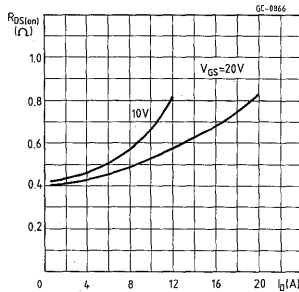## Output characteristics

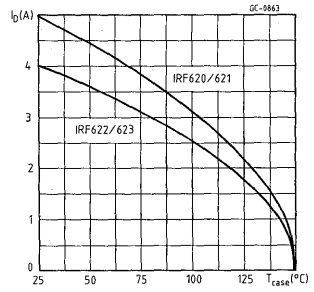## Output characteristics

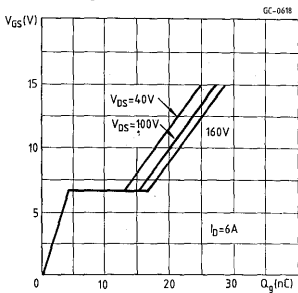## Transfer characteristics

Transconductance

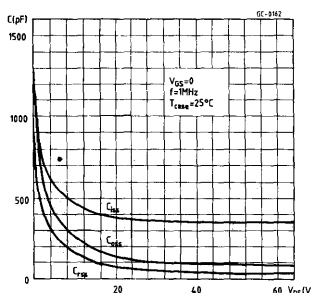## Static drain-source on resistance

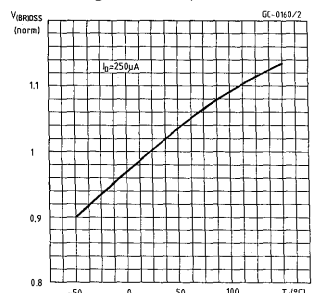## Maximum drain current vs temperature

Gate charge vs gate-source voltage

Capacitance variation

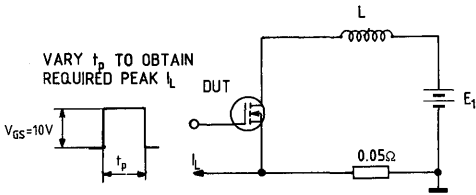## Normalized breakdown voltage vs temperature

SGS-THOMSON
MICROELECTRONICS

Normalized on resistance vs temperature

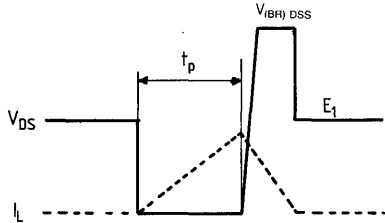## Source-drain diode forward characteristics

Unclamped inductive test circuit

SC-0339
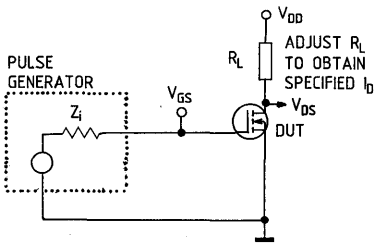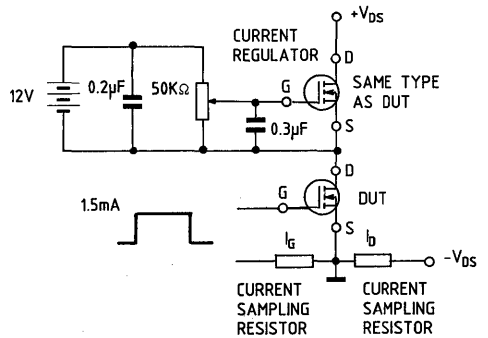
Unclamped inductive waveforms

SC-0338

Switching times test circuit

SC-0246

Gate charge test circuit

SC-0244

SGS-THOMSON
MICROELECTRONICS

ISOWATT220 PACKAGE CHARACTERISTICS AND APPLICATION.

ISOWATT220 is fully isolated to 2000V dc. Its thermal impedance, given in the data sheet, is optimised to give efficient thermal conduction together with excellent electrical isolation.

The structure of the case ensures optimum distances between the pins and heatsink. The ISOWATT220 package eliminates the need for external isolation so reducing fixing hardware. Accurate moulding techniques used in manufacture assure consistent heat spreader-to-heatsink capacitance.

ISOWATT220 thermal performance is better than that of the standard part, mounted with a 0.1mm mica washer. The thermally conductive plastic has a higher breakdown rating and is less fragile than mica or plastic sheets. Power derating for ISOWATT220 packages is determined by:

$$P_D = \frac{T_j - T_c}{R_{th}}$$

from this I_{Dmax} for the POWER MOS can be calculated:

$$I_{Dmax} \leqslant \sqrt{\frac{P_D}{R_{DS(on) \text{ (at } 150°C)}}}$$

THERMAL IMPEDANCE OF ISOWATT220 PACKAGE

Fig. 1 illustrates the elements contributing to the thermal resistance of transistor heatsink assembly, using ISOWATT220 package.

The total thermal resistance $R_{th \text{ (tot)}}$ is the sum of each of these elements.

The transient thermal impedance, Z_{th} for different pulse durations can be estimated as follows:

1 - for a short duration power pulse less than 1ms;

$$Z_{th} < R_{thJ-C}$$
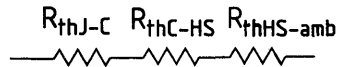
2 - for an intermediate power pulse of 5ms to 50ms:

$$Z_{th} = R_{thJ-C}$$

3 - for long power pulses of the order of 500ms or greater:
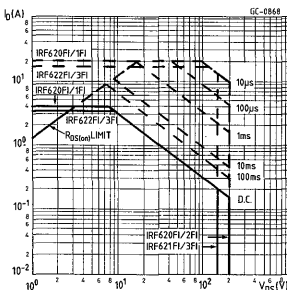
$$Z_{th} = R_{thJ-C} + R_{thC-HS} + R_{thHS-amb}$$

It is often possibile to discern these areas on transient thermal impedance curves.

Fig. 1
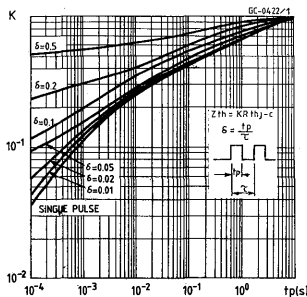

$$R_{thJ-C} \quad R_{thC-HS} \quad R_{thHS-amb}$$

ISOWATT DATA

Safe operating areas

Thermal impedance

Derating curve

SGS-THOMSON
MICROELECTRONICS